

Vishay Siliconix

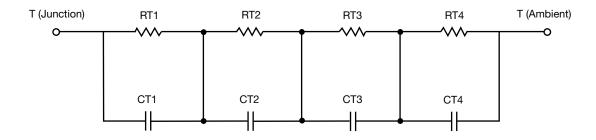
# **R-C Thermal Model Parameters**

### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

## **R-C THERMAL MODEL FOR TANK CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RT1	11.9104	502.8943m	N/A		
RT2	3.1921	15.0802m	N/A		
RT3	931.0195m	583.2510m	N/A		
RT4	23.9695	294.5329m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	8.2562	1.6224m	N/A		
CT2	1.0641	1.2770m	N/A		
CT3	147.3201m	26.7620m	N/A		
CT4	4.0108	223.9415m	N/A		

#### Note

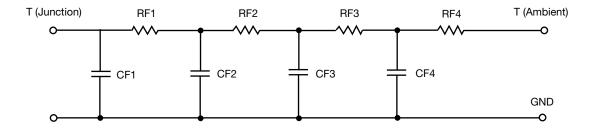
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

Revision: 16-Jun-11 Document Number: 63340



# **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RF1	884.7234m	598.4938m	N/A		
RF2	6.5762	715.7291m	N/A		
RF3	23.1425	86.5254m	N/A		
RF4	9.4830	2.2674m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	24.3391m	1.4181m	N/A		
CF2	882.6174m	27.2091m	N/A		
CF3	1.7594	2.7750	N/A		
CF4	2.6137	35.8850	N/A		

#### Note

• n/a indicates not applicable





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